

SOT-23 Plastic-Encapsulate MOSFETS

BC2300 N-Channel Enhancement Mode MOSFET

■ Features

- $V_{DS}=20V, R_{DS(ON)}=40m\Omega$ @ $V_{GS}=4.5V, I_D=5.0A$
- $V_{DS}=20V, R_{DS(ON)}=60m\Omega$ @ $V_{GS}=2.5V, I_D=4.0A$
- $V_{DS}=20V, R_{DS(ON)}=75m\Omega$ @ $V_{GS}=1.8V, I_D=1.0A$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and Maximum DC current capability

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain-Current	-Continuous * $T_J=125^\circ C$	I_D	3.8
		I_{DM}	15
-Pulsed			
Power Dissipation *	P_D	1.25	W
Thermal Resistance, Junction- to-Ambient	R_{thJA}	100	$^\circ C/W$
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 to 150	$^\circ C$

* Surface Mounted on FR 4 Board, $t \leq 10$ sec.

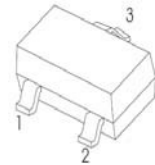
■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	μA
Gate-Body Leakage	I_{GSS}	$V_{GS} = \pm 10V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage *	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.6	0.78	1.5	V
Drain- Source on-state Resistance *	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=5.0A$		32	40	$m\Omega$
		$V_{GS}=2.5V, I_D=4.0A$		50	60	$m\Omega$
		$V_{GS}=1.8V, I_D=1.0A$		62	75	$m\Omega$
On-State Drain Current *	$I_{D(ON)}$	$V_{DS}=5V, V_{GS}=4.5V$	18			A
Forward Transconductance *	g_{FS}	$V_{DS}=5V, I_D=5A$	5			S
Input Capacitance	C_{ISS}	$V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz$		888		pF
Output Capacitance	C_{OSS}			144		pF
Reverse Transfer Capacitance	C_{RSS}			115		pF
Turn-On Delay Time	$t_{D(on)}$	$V_{DD}=10V, I_D=1A, V_{GS}=4.5V, R_L=10\Omega, R_{GEN}=6\Omega$		31.8		ns
Rise Time	t_r			14.5		ns
Turn-Off Delay Time	$t_{D(off)}$			50.3		ns
Fall Time	t_f			31.9		ns
Total Gate Charge	Q_g	$V_{DS} = 10V, I_D = 3.5A, V_{GS} = 4.5V$		16.8		nC
Gate-Source Charge	Q_{gs}			2.5		nC
Gate-Drain Charge	Q_{gd}			5.4		nC
Drain-Source Diode Forward Current *	I_S				1.25	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1.25A$		0.825	1.2	V

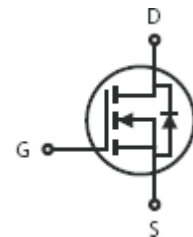
* Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

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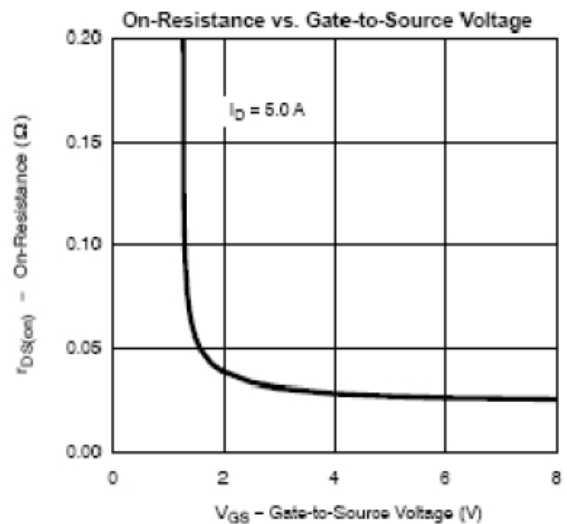
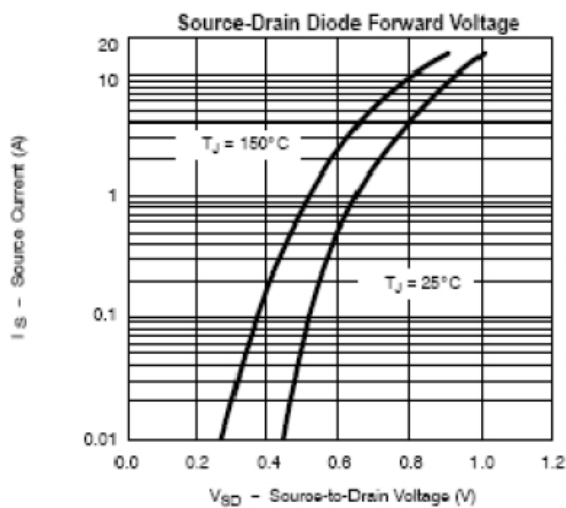
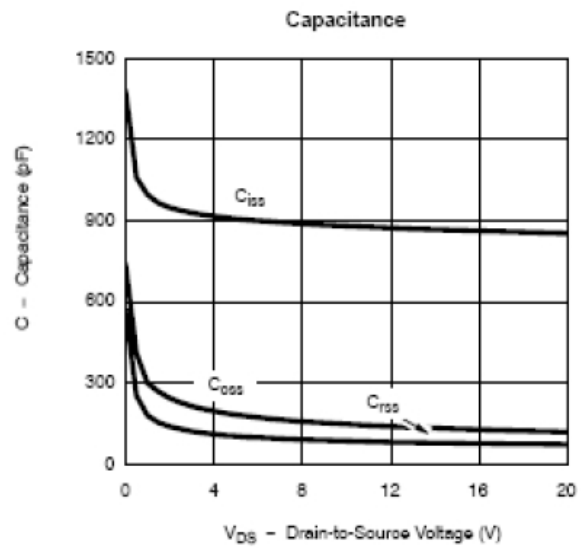
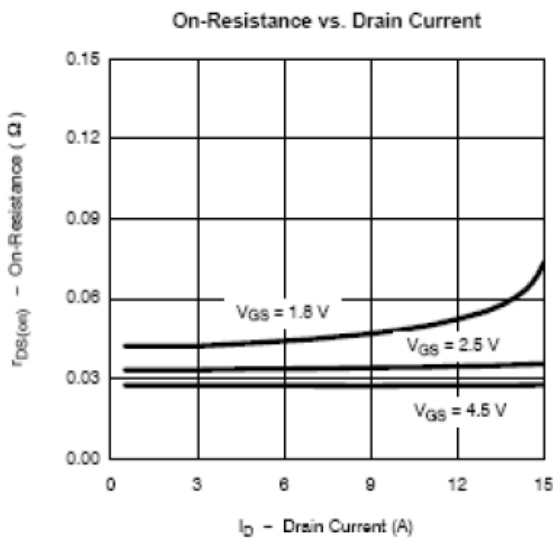
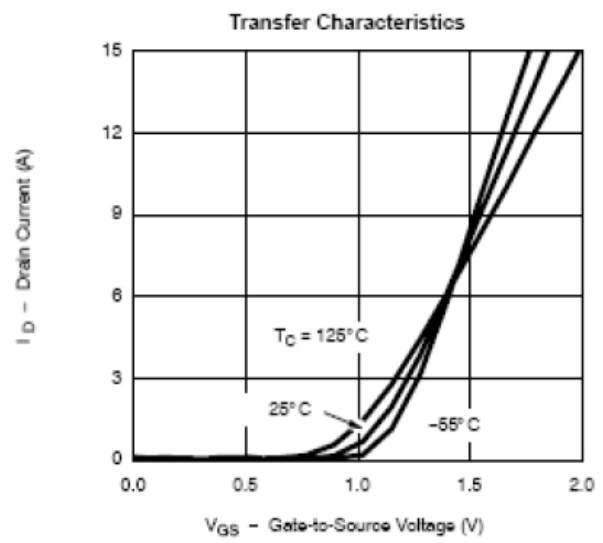
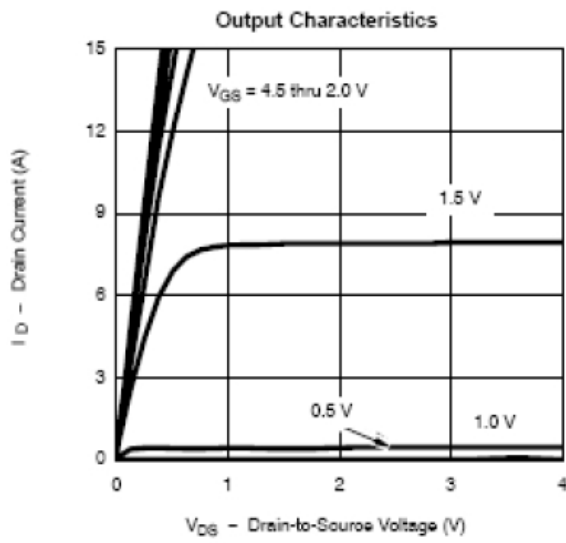
1. GATE
2. SOURCE
3. DRAIN



MARKING: 2300



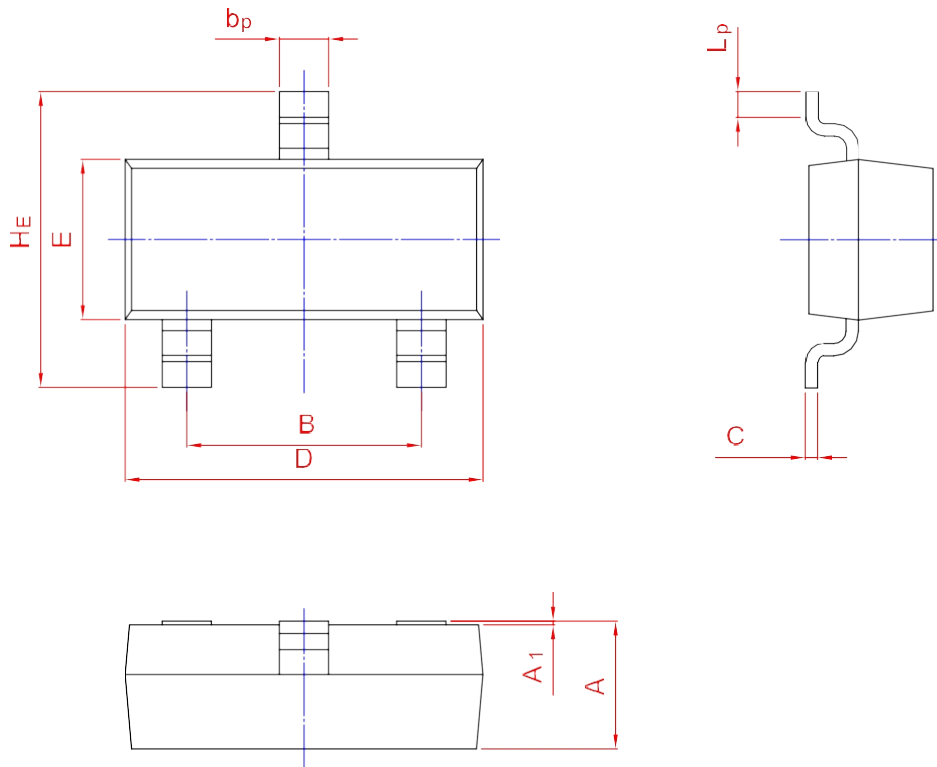
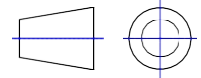
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

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UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20